





# YJB70G10A

## Electrical Characteristics ( $T_j=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V$			1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=20V, V_{DS}=0V$			100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.8	3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		7.2	8.6	m
		$V_{GS}=4.5V, I_D=20A$		8.8	11	m
Diode Forward Voltage	$V_{SD}$	$I_S=20A, V_{GS}=0V$			1.3	V



Typical Performance Characteristics

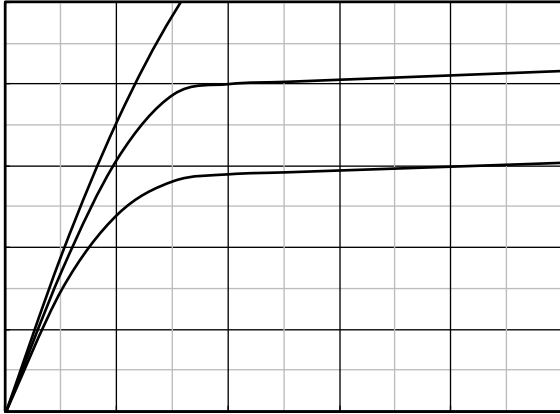




Figure7. Drain current

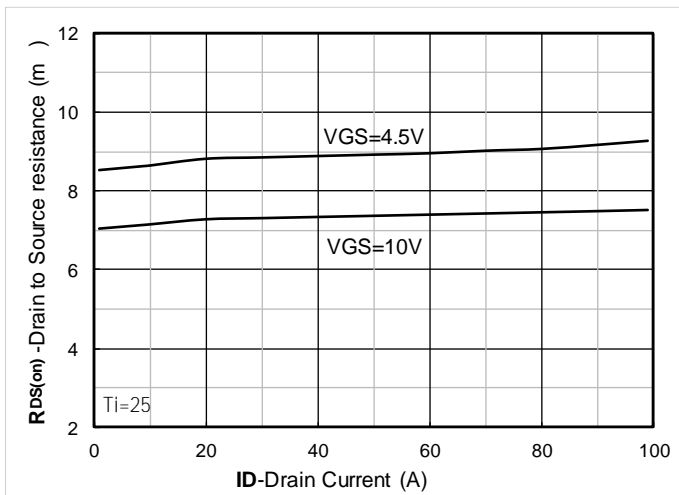


Figure 9.  $R_{DS(on)}$  VS Drain Current

Figure8.Safe Operation Area

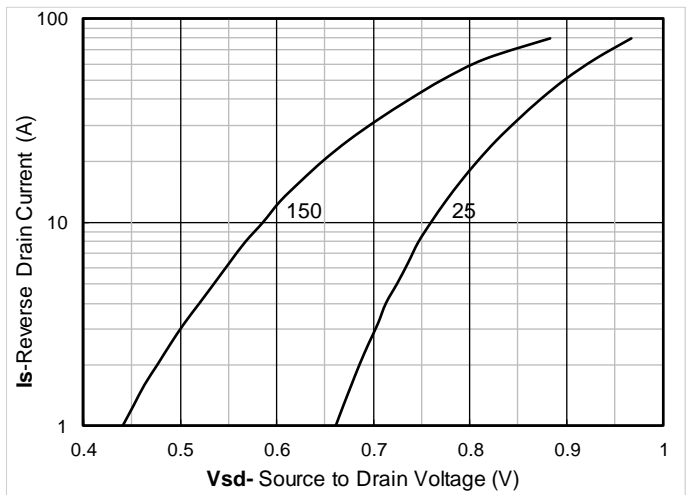


Figure 10. Forward characteristics of reverse diode

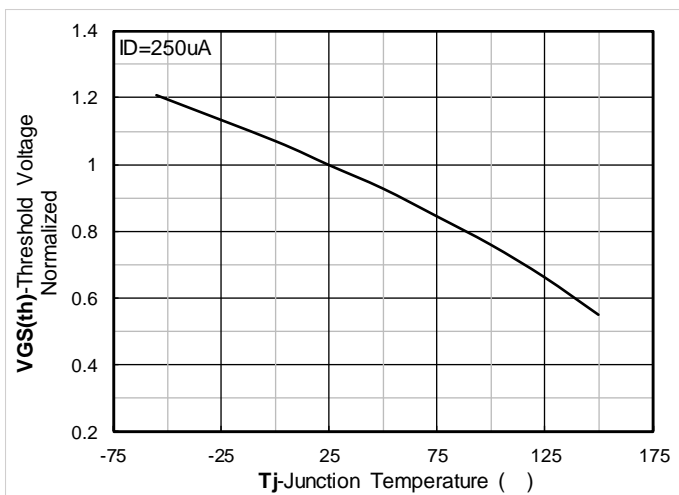
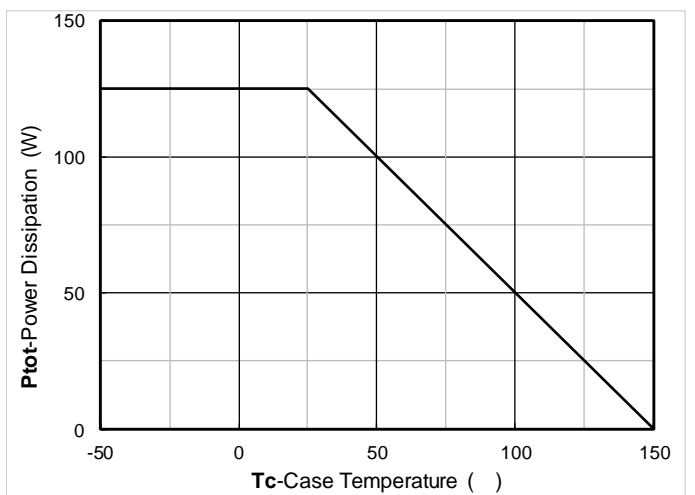


Figure 1





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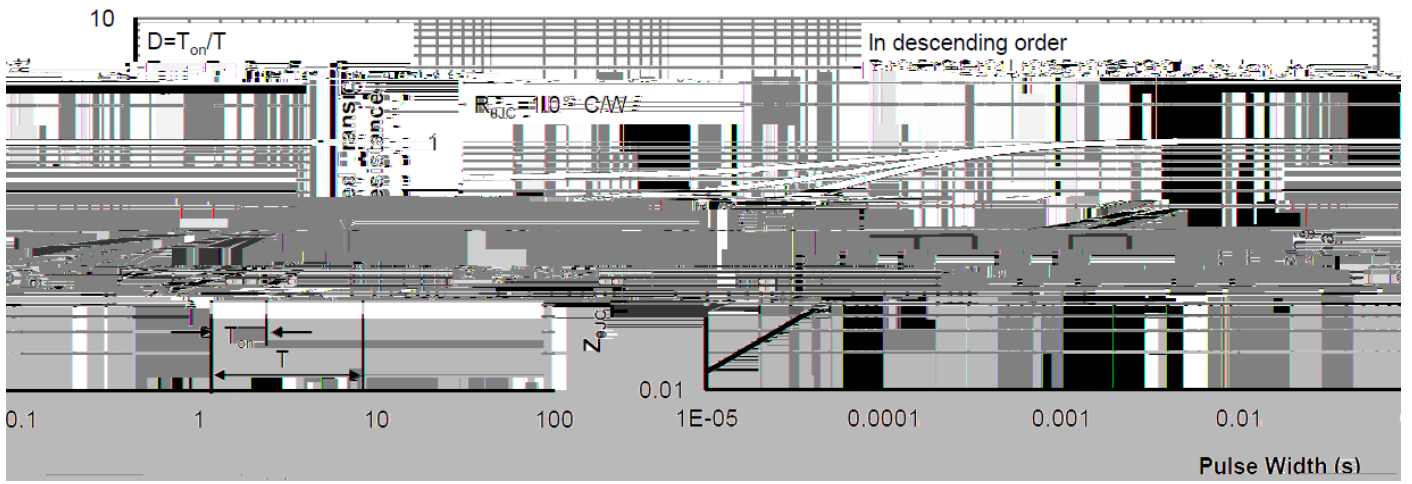


Figure13.Normalized Maximum Transient thermal impedance



TO-263-HY Package information

SYM.	MIN.
A2	
b2	0.050
c	
c2	
D2	
E	
E1	

